

Vishay Siliconix

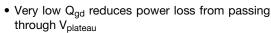
# N-Channel 100 V (D-S) MOSFET



PRODUCT SUMMARY			
V <sub>DS</sub> (V)	100		
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0040		
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.0045		
Q <sub>g</sub> typ. (nC)	84		
I <sub>D</sub> (A)	150 <sup>d</sup>		
Configuration	Single		

#### **FEATURES**

- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature

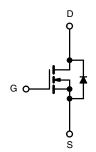




- 100 % R<sub>a</sub> and UIS tested
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **APPLICATIONS**

- Switching power supply
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing / e-fuse



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and halogen-free	SUM70042E-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	100	V	
Gate-source voltage		V <sub>GS</sub>	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Continuous drain surrent (T = 150 °C)	T <sub>C</sub> = 25 °C	150 d	150 <sup>d</sup>		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	139	A	
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	200	<b>7</b>	
Avalanche current		I <sub>AS</sub>	50		
Single avalanche energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Maximum nauray dissination 8	T <sub>C</sub> = 25 °C	278 b	278 <sup>b</sup>	W	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	178 <sup>b</sup>		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient (PCB mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W
Junction-to-case (drain)	R <sub>thJC</sub>	0.55	J 6/VV

#### Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}$	100	-	-	V	
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V	
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μА	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	150		
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	5	mA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50	-	-	Α	
During a second of the second	_	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.0033	0.0040	Ω	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 15 A	-	0.0036	0.0045		
Forward transconductance a	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A	-	60	-	S	
Dynamic <sup>b</sup>				•			
Input capacitance	C <sub>iss</sub>		-	6490	-		
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	570	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>		-	20	-		
Total gate charge <sup>c</sup>	Qg		-	84	110	nC	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	33.5	-		
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>		-	9.5	-		
Gate resistance	Rg	f = 1 MHz	0.26	1.3	2.6	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		-	25	50		
Rise time °	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_{L} = 5 \Omega$	-	18	36		
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	45	90	ns	
Fall time <sup>c</sup>	t <sub>f</sub>		-	14	28		
Drain-Source Body Diode Ratings	and Characte	ristics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Pulsed current (t = 100 μs)	I <sub>SM</sub>		-	-	200	Α	
Forward voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.5	V	
Reverse recovery time	t <sub>rr</sub>		-	58	116	ns	
Peak reverse recovery charge	I <sub>RM(REC)</sub>		-	3.9	5.9	Α	
Reverse recovery charge	Q <sub>rr</sub>	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	126	189	μC	
Reverse recovery fall time	t <sub>a</sub>		-	42	-	ns	
Reverse recovery rise time	t <sub>b</sub>		-	16	-	113	

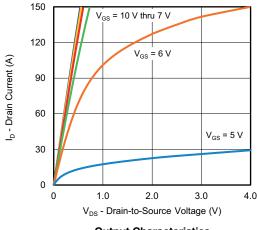
#### **Notes**

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

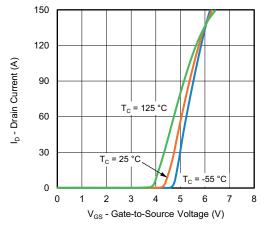
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



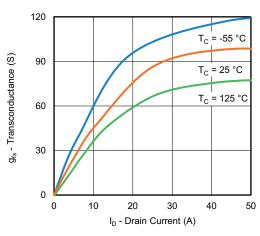
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



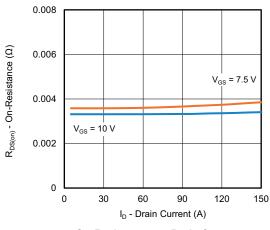
### **Output Characteristics**



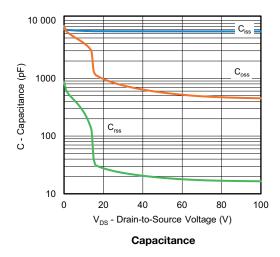
**Transfer Characteristics** 

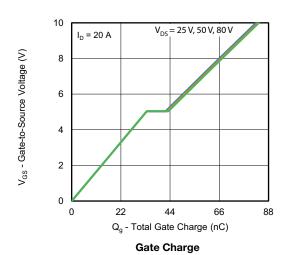


Transconductance



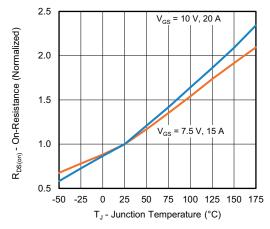
**On-Resistance vs. Drain Current** 



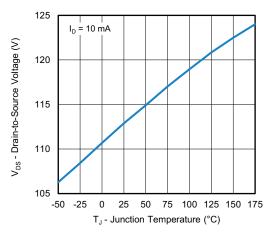




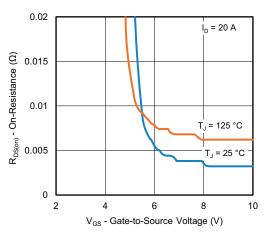
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



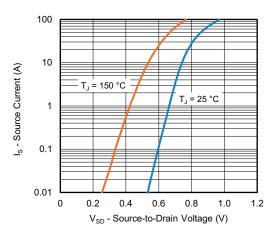
On-Resistance vs. Junction Temperature



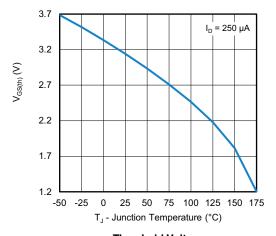
**Drain Source Breakdown vs. Junction Temperature** 



On-Resistance vs. Gate-to-Source Voltage

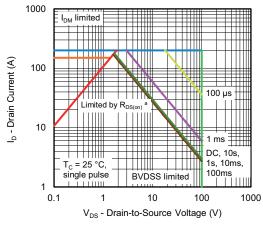


**Source Drain Diode Forward Voltage** 

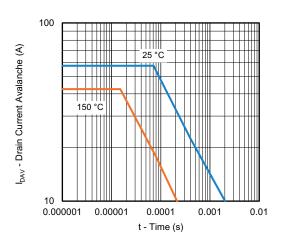




## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



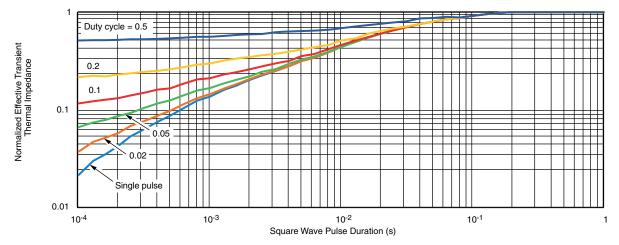




Single Pulse Avalanche Current Capability vs. Time

#### Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



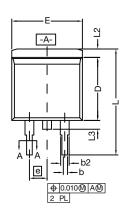
Normalized Thermal Transient Impedance, Junction-to-Case

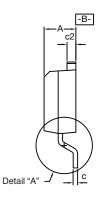
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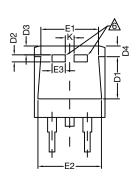
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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

### **VERSION 1: FACILITY CODE = T**

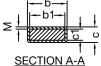








**DETAIL A (ROTATED 90°)** 



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### **Notes**

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

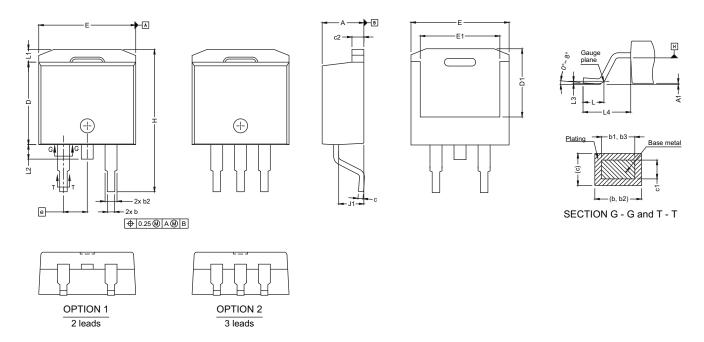
		INCHES		MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
Ci	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	BSC	2.54	BSC
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		L1 0.090		2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050



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### **VERSION 2: FACILITY CODE = N**



DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
С	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5	
E	10.15	10.55	
E1	8.1	8.7	
е	2.54	BSC	
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	- 1.78		
L3	0.25 typ.		
L4	4.78	5.28	
J1	2.56 2.96		

DWG: 5843





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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